

# 6V, 5A, 1.5MHz ACOT<sup>®</sup> Synchronous Step-Down Converter

## 1 General Description

The RT5779A/B is a simple, easy-to-use, 5A synchronous step-down converter with an input supply voltage range of 2.5V to 6V. The device builds in an accurate 0.6V ( $\pm 1.5\%$ ) reference voltage and can operate in 100% duty cycle as a very low dropout voltage regulator. The RT5779A/B integrates low RDS(ON) power MOSFETs to achieve high efficiency and is available in TSOT-23-8 (FC) package. The RT5779A/B adopts Advanced Constant On-Time (ACOT<sup>®</sup>) control architecture to provide an ultrafast transient response with few external components and to operate in nearly constant switching frequency over the line, load, and output voltage range. The RT5779A/B is designed to operate at 1.5MHz fixed frequency. While the RT5779A automatically enters power saving mode (PSM) operation at light load to maintain high efficiency. The RT5779B operates in Forced PWM over the loading range, that helps meet tight voltage regulation accuracy requirements.

The RT5779A/B senses the current in both MOSFETs for robust overcurrent protection. It prevents the device from the catastrophic damage in output short circuit, overcurrent, or inductor saturation. The individual enable control input and power-good indicator provides flexible system power sequence control a built-in soft-start function prevents inrush current during start-up. The device also includes input undervoltage-lockout, output undervoltage protection, and over-temperature protection (thermal shutdown) to provide safe and smooth operation in all operating conditions. The recommended junction temperature range is  $-40^{\circ}\text{C}$  to  $125^{\circ}\text{C}$ , and the ambient temperature range is  $-40^{\circ}\text{C}$  to  $85^{\circ}\text{C}$ .

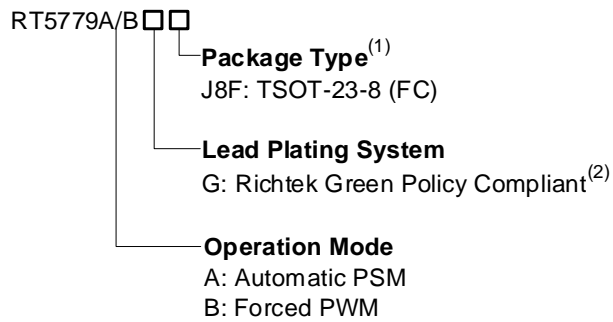
## 2 Features

- **5A Converter with Built-In 20m $\Omega$ /18m $\Omega$  Low RDS(ON) Power MOSFETs**
- **Input Supply Voltage Range: 2.5V to 6V**
- **Output Voltage Range: 0.6V to 6V**
- **Operates Up to 100% Duty Cycle**
- **Advanced Constant On-Time (ACOT<sup>®</sup>) Control**
- **Ultrafast Transient Response**
- **No Needs for External Compensation**
- **Optimized for Low-ESR Ceramic Output Capacitors**
- **0.6  $\pm 1.5\%$  High-Accuracy Feedback Reference Voltage**
- **35 $\mu$ A Operation Quiescent Current (RT5779A)**
- **Robust Current-Limit Protection for Both MOSFETs**
- **Optional for Operation Modes:**
  - **Power Saving Mode (PSM) (RT5779A)**
  - **Forced PWM Mode (RT5779B)**
- **Fixed Switching Frequency: 1.5MHz**
- **Monotonic Start-Up for Pre-Biased Output**
- **Individual Enable Control Input**
- **Power-Good Indicator**
- **Built-In Internally Fixed Soft-Start (Typical 1.5ms)**
- **100% Duty Cycle Mode**
- **Internal Output Discharge**
- **Input Undervoltage-Lockout (UVLO)**
- **Output Undervoltage Protection (UVP) with Hiccup Mode**
- **Over-Temperature Protection**
- **Available in TSOT-23-8 (FC) Package**

## 3 Applications

- WLAN ASIC Power/Storages (SSD and HDD)
- Mobile Phones and Handheld Devices
- Set-Top Boxes, Cable Modems, and xDSL Platforms
- General Purpose for POL LV Buck Converters

## 4 Ordering Information

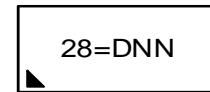


### Note 1.

- Marked with (1) indicated: Compatible with the current requirements of IPC/JEDEC J-STD-020.
- Marked with (2) indicated: Richtek products are Richtek Green Policy compliant.

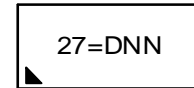
## 5 Marking Information

RT5779AGJ8F



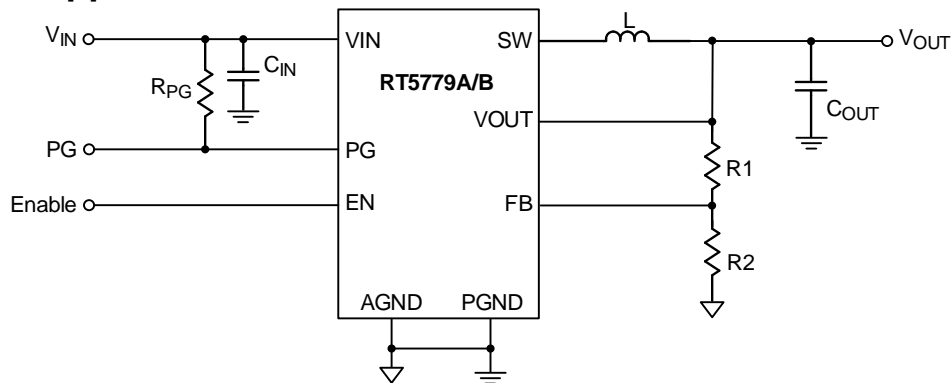
28= : Product Code  
DNN : Date Code

RT5779BGJ8F



27= : Product Code  
DNN : Date Code

## 6 Simplified Application Circuit

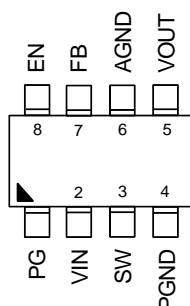


# Table of Contents

<b>1</b>	<b>General Description</b>	<b>1</b>	<b>18</b>	<b>Application Information</b>	<b>16</b>
<b>2</b>	<b>Features</b>	<b>1</b>	18.1	100% Duty-Cycle	16
<b>3</b>	<b>Applications</b>	<b>1</b>	18.2	Inductor Selection	16
<b>4</b>	<b>Ordering Information</b>	<b>2</b>	18.3	Input Capacitor Selection	17
<b>5</b>	<b>Marking Information</b>	<b>2</b>	18.4	Output Capacitor Selection	18
<b>6</b>	<b>Simplified Application Circuit</b>	<b>2</b>	18.5	EN Pin for Start-Up and Shutdown Operation	19
<b>7</b>	<b>Pin Configuration</b>	<b>4</b>	18.6	Output Voltage Setting	19
<b>8</b>	<b>Functional Pin Description</b>	<b>4</b>	18.7	Thermal Considerations	20
<b>9</b>	<b>Functional Block Diagram</b>	<b>5</b>	18.8	Layout Considerations	21
<b>10</b>	<b>Absolute Maximum Ratings</b>	<b>6</b>	<b>19</b>	<b>Outline Dimension</b>	<b>23</b>
<b>11</b>	<b>ESD</b>	<b>6</b>	<b>20</b>	<b>Footprint Information</b>	<b>24</b>
<b>12</b>	<b>Recommended Operating Conditions</b>	<b>6</b>	<b>21</b>	<b>Packing Information</b>	<b>25</b>
<b>13</b>	<b>Thermal Information</b>	<b>6</b>	21.1	Tape and Reel Data	25
<b>14</b>	<b>Electrical Characteristics</b>	<b>7</b>	21.2	Tape and Reel Packing	26
<b>15</b>	<b>Typical Application Circuit</b>	<b>9</b>	21.3	Packing Material Anti-ESD Property	27
<b>16</b>	<b>Typical Operating Characteristics</b>	<b>10</b>	<b>22</b>	<b>Datasheet Revision History</b>	<b>28</b>
<b>17</b>	<b>Operation</b>	<b>12</b>			
17.1	Low $V_{IN}$ ACOT <sup>®</sup> One-Shot Operation	12			
17.2	Enable Control	12			
17.3	Input Undervoltage-Lockout	12			
17.4	Current-Limit Protection	13			
17.5	Output Undervoltage Protection	13			
17.6	Hiccup Mode	14			
17.7	Soft-Start	14			
17.8	Power-Good Function	15			
17.9	Over-Temperature Protection	15			

## 7 Pin Configuration

(TOP VIEW)

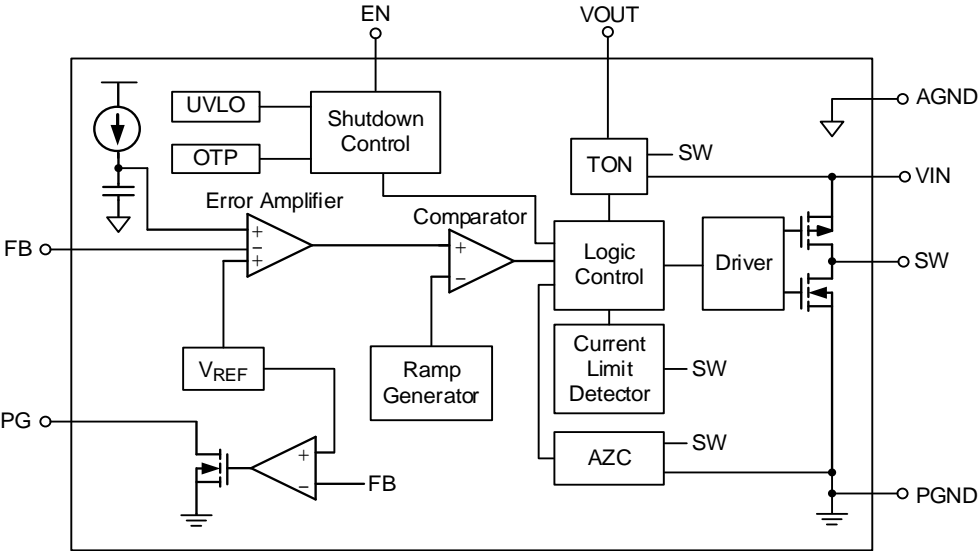


TSOT-23-8 (FC)

## 8 Functional Pin Description

Pin No.	Pin Name	Pin Function
1	PG	Open-drain power-good indication output. The power-good function is activated after the soft-start is finished.
2	VIN	Power input. The input voltage range is from 2.5V to 6V. Connect a suitable input bypass capacitor (typically greater than 10 $\mu$ F) between this pin and PGND. The bypass capacitor should be placed as close to the IC as possible.
3	SW	Switch node between the internal switch and the synchronous rectifier. Connect the output LC filter from this pin to the output load.
4	PGND	Power ground. This pin, connected to analog ground, must be soldered to a large PCB copper area for maximum power dissipation.
5	VOUT	Output voltage sense input. This pin is used to monitor and adjust the output voltage to enhance load transient regulation.
6	AGND	Analog ground. It provides a ground return path for the control circuitry and internal reference. Connect AGND to a clean inner GND point with a separate trace.
7	FB	Feedback voltage input. Connect this pin to the midpoint of the external feedback resistive divider to set the output voltage of the converter to the desired regulation level. The device regulates the FB voltage at a feedback reference voltage, typically 0.6V.
8	EN	Enable control input. A logic-high enables the converter; a logic-low forces the device into shutdown mode.

9 Functional Block Diagram



## 10 Absolute Maximum Ratings

([Note 2](#))

- Supply Input Voltage, VIN ----- -0.3V to 7V
- SW Pin Switch Voltage----- -0.3V to (VIN + 0.3V)
- <10ns ----- -5V to 8.5V
- Other Pins ----- -0.3V to (VIN + 0.3V)
- Junction Temperature ----- 150°C
- Lead Temperature (Soldering, 10 sec.) ----- 260°C
- Storage Temperature Range ----- -65°C to 150°C

**Note 2.** Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions may affect device reliability.

## 11 ESD

([Note 3](#))

- ESD Susceptibility  
HBM (Human Body Model) -----2kV

**Note 3.** Devices are ESD sensitive. Handling precautions are recommended.

## 12 Recommended Operating Conditions

([Note 4](#))

- Supply Input Voltage, VIN -----2.5V to 6V
- Junction Temperature Range----- -40°C to 125°C
- Ambient Temperature Range----- -40°C to 85°C

**Note 4.** The device is not guaranteed to function outside its operating conditions.

## 13 Thermal Information

([Note 5](#) and [Note 6](#))

Thermal Parameter		TSOT-23-8 (FC)	Unit
$\theta_{JA}$	Junction-to-ambient thermal resistance (JEDEC standard)	95.2	°C/W
$\theta_{JC(Top)}$	Junction-to-case (top) thermal resistance	3.3	°C/W
$\theta_{JC(Bottom)}$	Junction-to-case (bottom) thermal resistance	4.6	°C/W
$\theta_{JA(EVB)}$	Junction-to-ambient thermal resistance (specific EVB)	73.9	°C/W
$\Psi_{JC(Top)}$	Junction-to-top characterization parameter	13	°C/W
$\Psi_{JB}$	Junction-to-board characterization parameter	53.8	°C/W

**Note 5.** For more information about thermal parameter, see the Application and Definition of Thermal Resistances report, [AN061](#).

**Note 6.**  $\theta_{JA(EVB)}$ ,  $\Psi_{JC(TOP)}$ , and  $\Psi_{JB}$  are measured on a high effective-thermal-conductivity four-layer test board with dimensions of 55.9mm x 50mm; furthermore, all layers are made with 2 oz. Cu. Thermal resistance/parameter values may vary depending on the PCB material, layout, and test environmental conditions.

## 14 Electrical Characteristics

( $V_{IN} = 5V$ ,  $T_A = 25^{\circ}C$ , unless otherwise specified.)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Supply Voltage						
VIN Supply Input Voltage	VIN		2.5	--	6	V
Undervoltage-Lockout Rising Threshold	VUVLO_R		2.15	2.3	2.45	
Undervoltage-Lockout Hysteresis	VUVLO_HYS		--	260	--	mV
Shutdown Current	ISHDN	VEN = 0V	--	0	1	μA
Quiescent Current	IQ	RT5779A	--	35	50	μA
		RT5779B	--	600	--	
Enable Voltage						
EN Input Voltage Rising Threshold	VEN_R	VEN rising	1.2	--	--	V
EN Input Voltage Falling Threshold	VEN_F	VEN falling	--	--	0.4	V
Enable Input Current	IEN	VEN = 2V	--	1.5	--	μA
		VEN = 0V	--	0	--	
Feedback Voltage						
Feedback Input Current	IFB	VFB = 0.6V	--	10	--	nA
Feedback Voltage	VFB		0.591	0.6	0.609	V
Current Limit						
High-Side Switch Current Limit	ILIM_H		--	9.7	--	A
Low-Side Switch Current Limit	ILIM_L		6	7.5	9.1	
Switching						
Switching Frequency	fsw	VOUT = 1.2V	1300	1500	1700	kHz
Minimum Off-Time	toff_MIN		--	60	--	ns
Internal MOSFET						
On-Resistance of High-Side MOSFET	Rdson_H		--	18	--	mΩ
On-Resistance of Low-Side MOSFET	Rdson_L		--	16	--	
Soft-Start						
Soft-Start Time	tss	0% to 95% of the target VOUT	1	1.5	--	ms
EN to PG Delay Time	tdly_EN_PG		1	2.5	4	ms
Output Discharge						
Output Discharge Resistor	Rdischg		--	1	--	kΩ
Power-Good Function						
Power-Good High Threshold	VPg_H	VFB rising. PG goes high.	--	95	--	%VFB

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Power-Good High Hysteresis	V <sub>PG_H_HYS</sub>	V <sub>FB</sub> falling. PG goes low.	--	5	--	%V <sub>FB</sub>
Power-Good Low Threshold	V <sub>PG_L</sub>	V <sub>FB</sub> rising. PG goes low.	--	110	--	%V <sub>FB</sub>
Power-Good Low Hysteresis	V <sub>PG_L_HYS</sub>	V <sub>FB</sub> falling. PG goes high.	--	5	--	%V <sub>FB</sub>
Power-Good Falling Delay Time	t <sub>DLY_PG_F</sub>	V <sub>PG</sub> delay. PG goes low.	--	15	--	μs
Power-Good Sink Current Capability		I <sub>PG</sub> sinks 1mA	--	--	0.4	V
Power-Good Internal Pull Up Resistance			--	550	--	kΩ
<b>Over-Temperature Protection</b>						
Over-Temperature Protection Threshold	T <sub>OTP</sub>		--	150	--	°C
Over-Temperature Protection Hysteresis	T <sub>OTP_HYS</sub>		--	30	--	

15 Typical Application Circuit

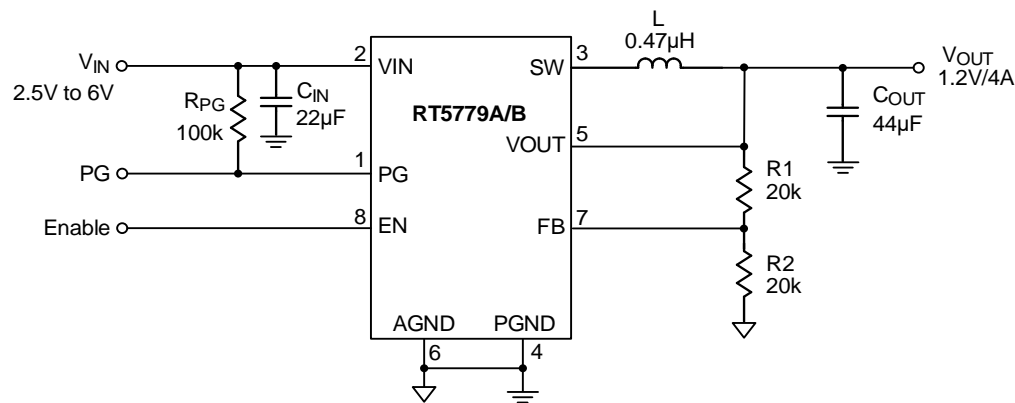
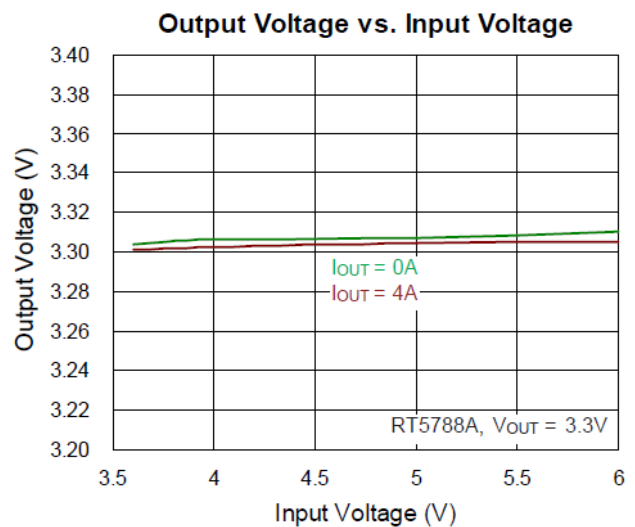
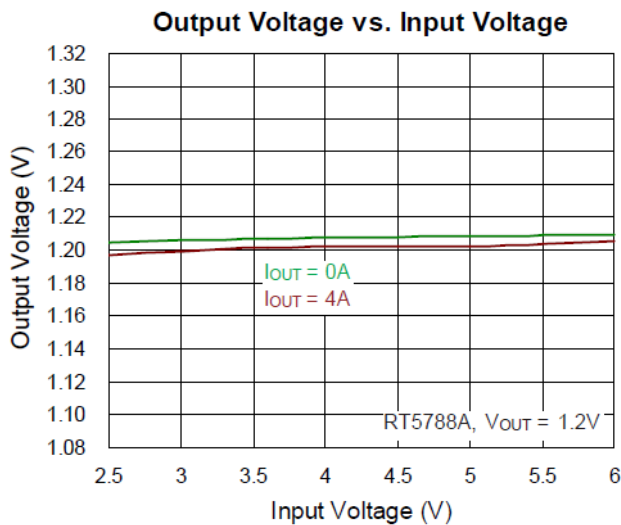
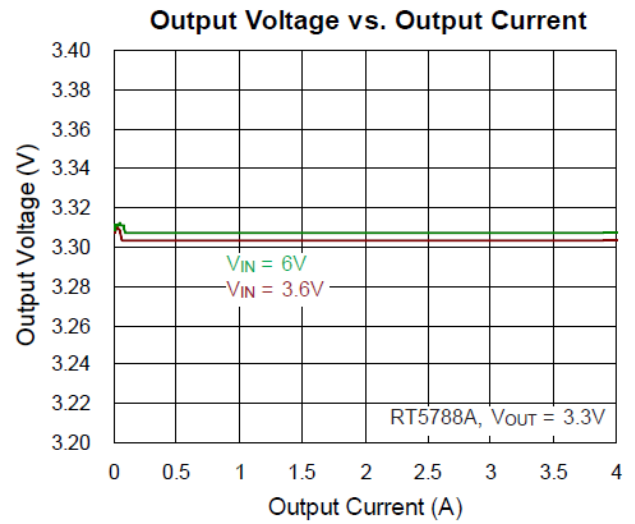
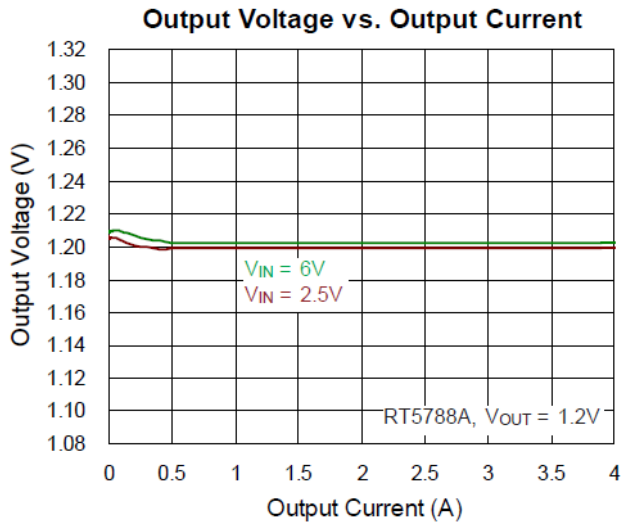
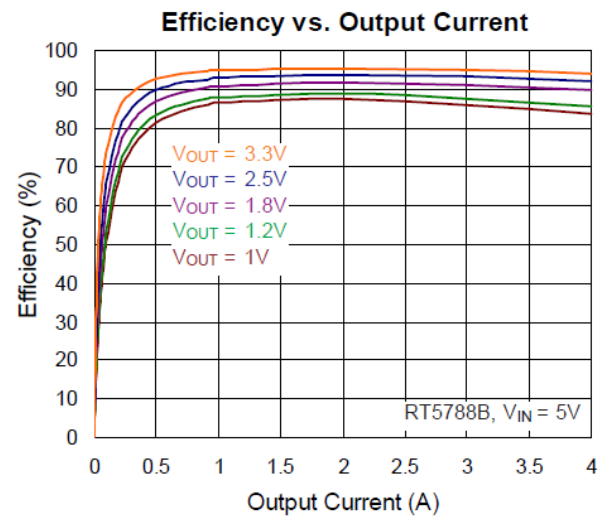
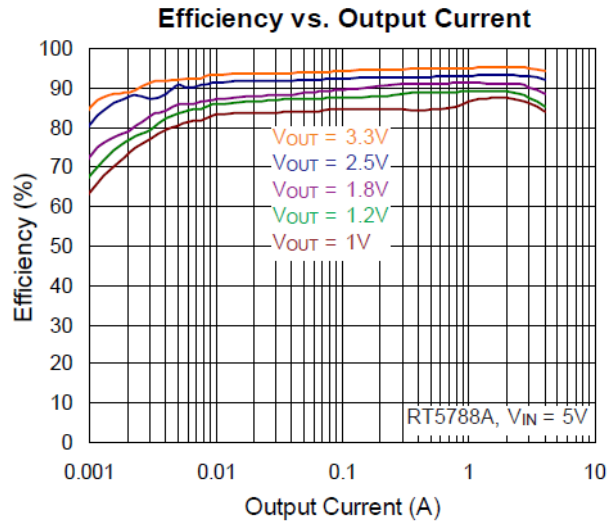
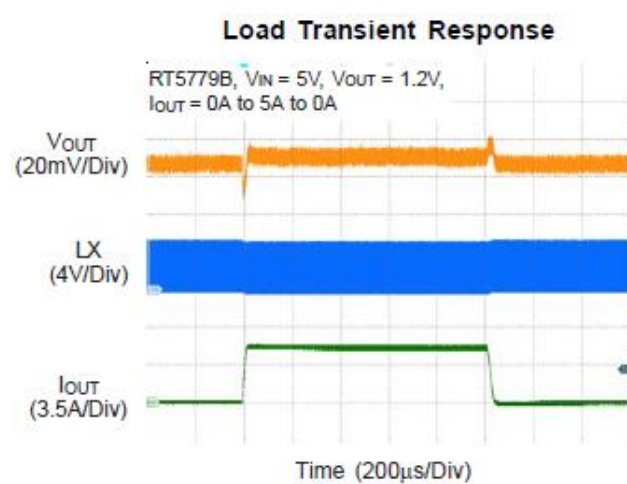
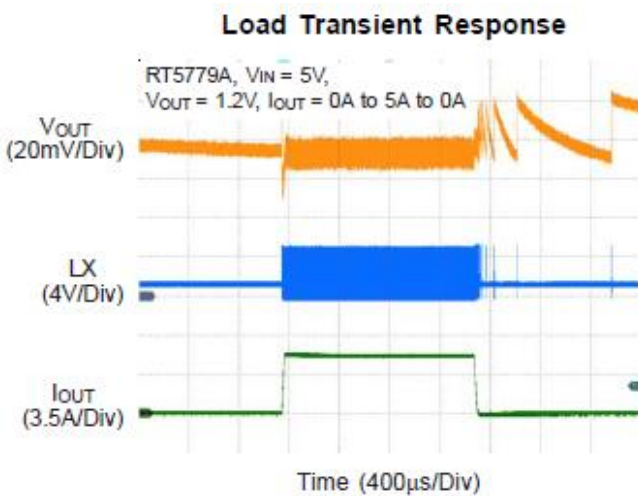
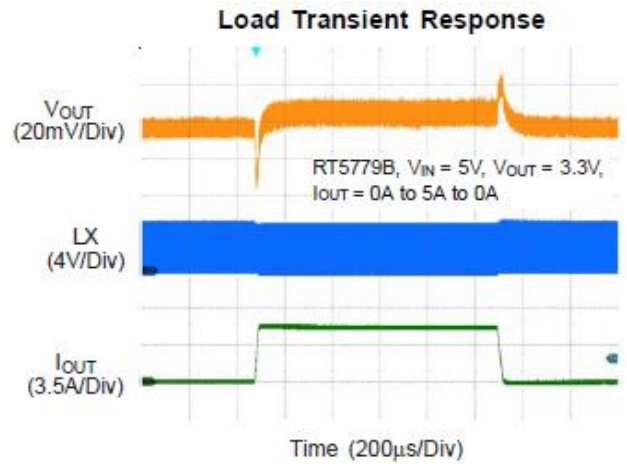
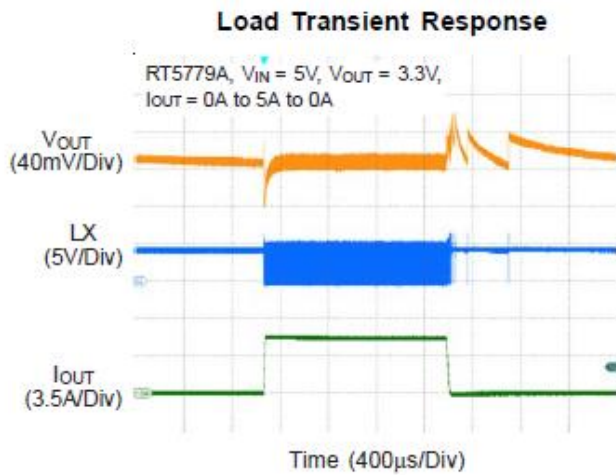
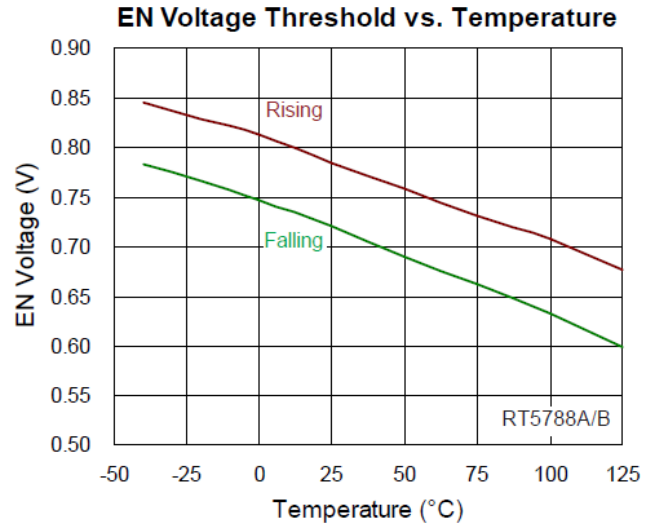
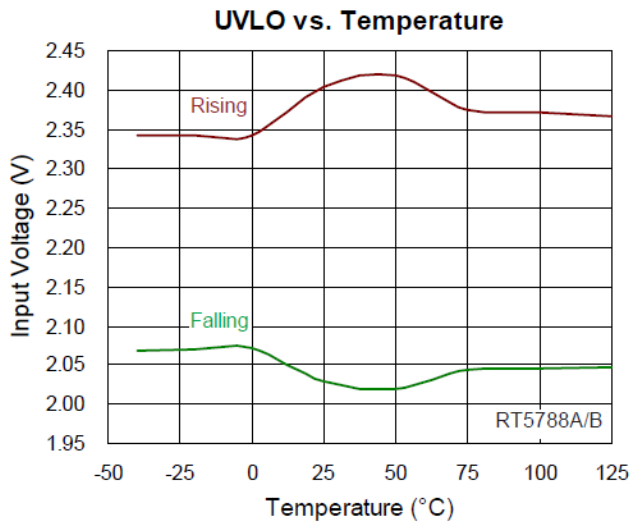


Table 1. Suggested Component Values

V <sub>OUT</sub> (V)	R <sub>1</sub> (kΩ)	R <sub>2</sub> (kΩ)	L (μH)	C <sub>OUT</sub> (μF)
1	13.3	20	0.33	44
1.2	20	20	0.47	44
1.8	40.2	20	0.47	44
2.5	63.4	20	0.47	44
3.3	90.9	20	0.47	44

## 16 Typical Operating Characteristics





## 17 Operation

The RT5779A/B is a high-efficiency, synchronous step-down converter designed for low-voltage applications. It supports a wide input supply range from 2.5V to 6V and is capable of delivering up to 5A output current. Utilizing ACOT<sup>®</sup> control mode, the RT5779A/B significantly reduces the need for output capacitance, enabling ultrafast transient responses and allowing for minimal component sizes without the necessity of an external compensation network. The device features an integrated ramp voltage generator that uses the virtual inductor current as input. This internal ramp signal allows for effective compensation and ensures stability with low-ESR ceramic capacitors by eliminating the requirement for an ESR ramp voltage generated by the output capacitor's ESR.

### 17.1 Low $V_{IN}$ ACOT<sup>®</sup> One-Shot Operation

For a low  $V_{IN}$  ACOT<sup>®</sup> converter, a built-in error amplifier is used to monitor the feedback voltage, as illustrated in the [Functional Block Diagram](#) section. In steady state, the error amplifier compares the feedback voltage  $V_{FB}$  with an internal reference voltage. If the virtual inductor current ramp voltage is lower than the output of the error amplifier, a new pre-determined fixed on-time will be triggered by the on-time one-shot generator, provided that the minimum off-time one-shot is cleared and the measured inductor current through the synchronous rectifier (low-side switch) is below the current limit  $I_{LIM\_L}$ . During the on-time, the high-side switch is turned on, and the inductor current ramps up linearly. After the on-time, the high-side switch is turned off, and the synchronous rectifier is turned on, allowing the inductor current to ramp down linearly. If the output voltage has not reached its nominal level, another on-time can only be generated after a short blanking time, known as the minimum off-time, which is triggered by the minimum-off-time one-shot generator. This is to prevent another immediate on-time from being triggered during the noisy switching time and to allow the feedback voltage and current sense signals to settle. The minimum off-time  $t_{OFF\_MIN}$  is kept short so that the inductor current can be quickly raised by rapidly repeated on-times when needed. This feature enhances the reaction speed of ACOT<sup>®</sup>-based converters to load transients significantly.

### 17.2 Enable Control

The RT5779A/B provides an EN pin as an external chip enable control to enable or disable the device. If  $V_{EN}$  is held below a falling threshold voltage ( $V_{EN\_F}$ ) of the enable input (EN), the converter will enter shutdown mode, disabling the converter and inhibiting switching even if the  $V_{IN}$  voltage is above the  $V_{IN}$  undervoltage-lockout rising threshold ( $V_{UVLO\_R}$ ). During shutdown mode, the supply current can be reduced to  $I_{SHDN}$  (1 $\mu$ A or below). If  $V_{EN}$  rises above the rising threshold voltage ( $V_{EN\_R}$ ) while the  $V_{IN}$  is higher than the UVLO rising threshold ( $V_{UVLO\_R}$ ), the device will be turned on, enabling switching and initiating the soft-start sequence.

### 17.3 Input Undervoltage-Lockout

In addition to the EN pin, the RT5779A/B also provides enable control through the input voltage  $V_{IN}$  pin. It features an undervoltage-lockout (UVLO) function that monitors the internal linear regulator ( $V_{CC}$ ). If  $V_{EN}$  rises above  $V_{EN\_H}$  first, switching will still be inhibited until the  $V_{IN}$  voltage rises above  $V_{UVLO\_R}$ . This is to ensure that the internal regulator is ready, preventing operation with not-fully-enhanced internal MOSFET switches. After the device is powered up, if the input voltage  $V_{IN}$  falls below the UVLO falling threshold voltage ( $V_{UVLO\_R} - V_{UVLO\_HYS}$ ), switching will be inhibited; if  $V_{IN}$  rises above the UVLO rising threshold ( $V_{UVLO\_R}$ ), the device will resume switching.

### 17.4 Current-Limit Protection

The RT5779A/B features cycle-by-cycle current-limit protection on both the high-side and low-side MOSFETs and the protection prevents the device from catastrophic damage in an output short circuit, overcurrent, or inductor saturation.

The high-side MOSFET current-limit protection is achieved by an internal current comparator that monitors the current in the high-side MOSFET during each on-time. The switch current is compared with the high-side switch peak current-limit threshold ( $I_{LIM\_H}$ ) after a certain delay when the high-side switch is turned on each cycle. If a current-limit condition occurs, the converter will immediately turn off the high-side switch and turn on the low-side switch to prevent the inductor current from exceeding the high-side current limit.

The low-side MOSFET current-limit protection is achieved by measuring the inductor current through the synchronous rectifier (low-side switch) during the low-side on-time. Once the current rises above the low-side switch valley current-limit threshold ( $I_{LIM\_L}$ ), the on-time one-shot will be inhibited until the inductor current ramps down to the current limit threshold ( $I_{LIM\_L}$ ), that is, another on-time can only be triggered when the inductor current goes below the low-side current limit. If the output load current exceeds the available inductor current (clamped by the low-side current limit), the output capacitor needs to supply the extra current such that the output voltage will begin to drop. If it drops below the output undervoltage protection threshold, the IC will stop switching to avoid excessive heat. [Figure 1](#) shows the current-limit protection of the RT5779A/B.

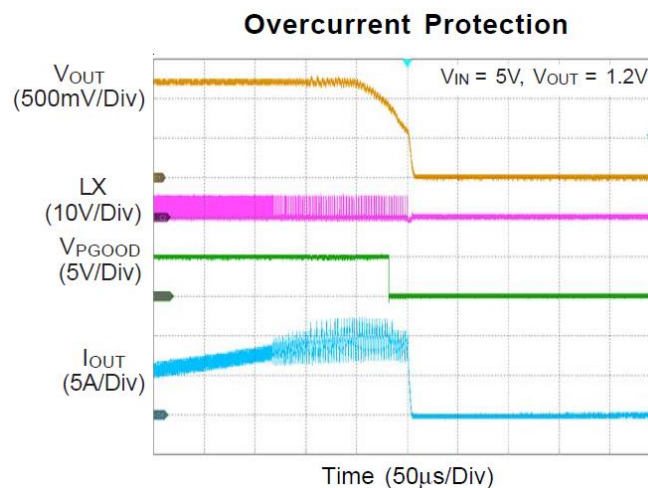


Figure 1. Current-Limit Protection

### 17.5 Output Undervoltage Protection

The RT5779A/B includes output undervoltage protection (UVP) against overload or short-circuit conditions by constantly monitoring the feedback voltage  $V_{FB}$ . If  $V_{FB}$  drops below the undervoltage protection threshold (typically 50% of the internal feedback reference voltage), the UV comparator will go high to turn off both the internal high-side and low-side MOSFET switches. The RT5779A/B will enter output undervoltage protection with hiccup mode. During hiccup mode, the IC will shut down for 3.5ms (typical), and then attempt to recover automatically for 1.2ms (typical). Upon completion of the soft-start sequence, if the fault condition is removed, the converter will resume normal operation; otherwise, this auto-recovery cycle will be repeated until the fault condition is cleared. Hiccup mode allows the circuit to operate safely with low input current and power dissipation, and then resume normal operation as soon as the overload or short-circuit condition is removed. A short-circuit protection and recovery profile is shown in the following figure.

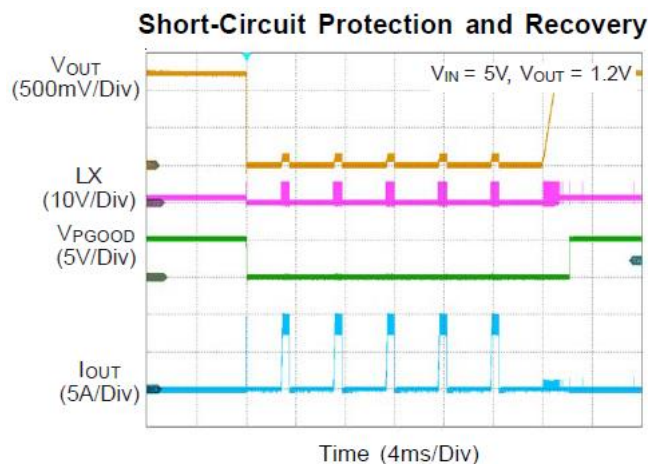


Figure 2. Short-Circuit Protection and Recovery

### 17.6 Hiccup Mode

If the output undervoltage condition continues for a period of time, the RT5779A/B will enter output undervoltage protection with hiccup mode. During hiccup mode, the device remains shut down. After a period of time, a soft-start sequence for auto-recovery will be initiated. Upon completion of the soft-start sequence, if the fault condition is removed, the converter will resume normal operation; otherwise, such cycle for auto-recovery will be repeated until the fault condition is cleared. Hiccup mode allows the circuit to operate safely with low input current and power dissipation, and then resume normal operation as soon as the overload or short-circuit condition is removed.

### 17.7 Soft-Start Function

The RT5779A/B features an internal soft-start mechanism designed to control inrush current. During power-up, the internal capacitor undergoes a charging process via an internal current source, resulting in the generation of a gradual soft-start ramp voltage. This ramp voltage serves as a reference voltage for the output tracking. The device begins switching operations, and the output voltage smoothly increases to its targeted regulation voltage. This transition occurs only when the ramp voltage exceeds the feedback voltage,  $V_{FB}$ . This mechanism ensures that the converters experience a seamless startup, particularly in scenarios with pre-biased outputs. The output voltage begins its ascent within  $100\mu\text{s}$  (typical) from the moment EN is asserted. Furthermore, the soft-start ramp-up time, defined as the period from 0% to 95% of target  $V_{OUT}$ , is typically 1.5ms.

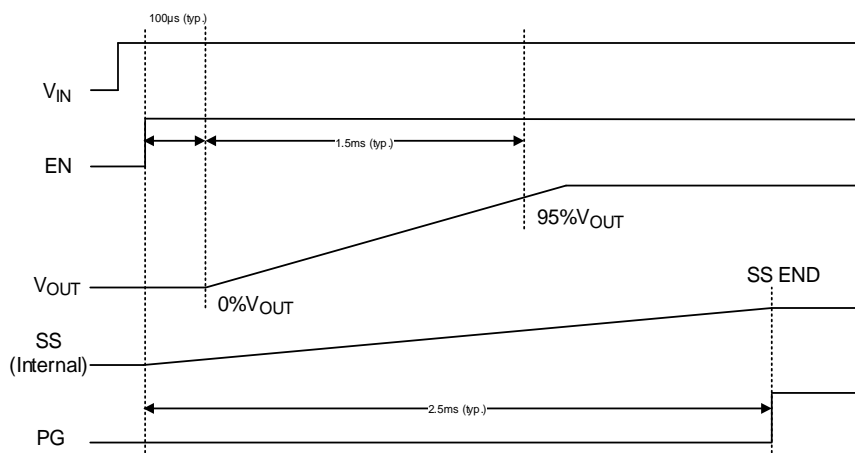


Figure 3. Start-Up Sequence

### 17.8 Power-Good Function

The RT5779A/B incorporates an open-drain power-good output (PG) that serves as a status indicator of the output voltage. The comparator's output delay plays a crucial role in preventing false flag operations in response to short excursions in the output voltage, such as those occurring during line and load transients. To configure the PG signal, it can be pulled up with a resistor to  $V_{IN}$  or an external voltage source, provided that the voltage does not exceed 6V.

The activation of the power-good function occurs after the completion of the soft-start and is controlled by a comparator connected to the feedback signal  $V_{FB}$ . When  $V_{FB}$  rises above a specified power-good high threshold ( $V_{PG\_H}$ ), typically set at 95% of the reference voltage, the PG pin enters a high-impedance state, and  $V_{PG}$  remains in a high state after a certain delay period. Conversely, when  $V_{FB}$  surpasses the  $V_{PG\_L}$  threshold (typically set at 110% of the reference voltage), the PG pin is pulled low.

In cases where  $V_{FB}$  exceeds  $V_{PG\_L}$  and subsequently drops back to a level below the power-good high threshold ( $V_{PG\_L} - V_{PG\_L\_HYS}$ ), typically set at 105% of the reference voltage,  $V_{PG}$  can be pulled high again. On the other hand, if  $V_{FB}$  falls below the power-good low threshold ( $V_{PG\_H} - V_{PG\_H\_HYS}$ ), typically set at 90% of the reference voltage, the PG pin is pulled low.

Furthermore, once the device is started up, if any internal protection mechanism is triggered, the PG signal will be pulled low to ground. A graphical representation of the power-good indication profile can be found in Figure 4.

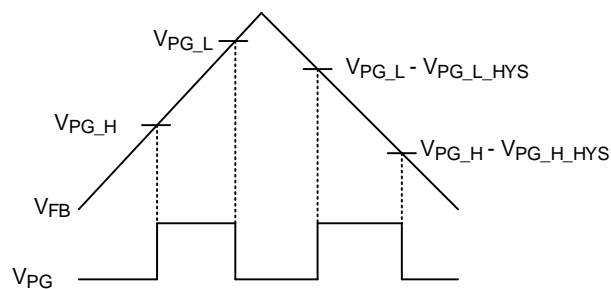


Figure 4. The Logic of PG

### 17.9 Over-Temperature Protection

The RT5779A/B includes an over-temperature protection (OTP) circuitry to prevent overheating due to excessive power dissipation. The OTP will shut down switching operation when the junction temperature exceeds a thermal shutdown threshold  $T_{OTP}$ . Once the junction temperature cools down by a thermal shutdown hysteresis ( $T_{OTP\_HYS}$ ), the IC will resume normal operation with a complete soft-start.

Note that the over-temperature protection is intended to protect the device during momentary overload conditions. The protection is activated outside the absolute maximum range of the operation as a secondary fail-safe and therefore should not be relied upon operationally. Continuous operation above the specified absolute maximum operating junction temperature may impair device reliability or permanently damage the device.

## 18 Application Information

(Note 7)

The output stage of a synchronous buck converter is composed of an inductor and a capacitor, which store and deliver energy to the load, and forms a second-order lowpass filter to smooth out the switch node voltage to maintain a regulated output voltage.

### 18.1 100% Duty-Cycle

When the input voltage drops, these buck converters gradually increase the duty-cycle and will continuously switch-on the high-side MOSFET when the input voltage drops below the regulated output voltage. This function is especially suitable in battery-powered applications and can extend the application operation time when the battery is almost depleted.

### 18.2 Inductor Selection

The inductor selection makes trade-offs among size, cost, efficiency, and transient response requirements. Generally, three key inductor parameters are specified for operation with the device: inductance value (L), inductor saturation current ( $I_{SAT}$ ), and DC resistance (DCR).

A good compromise between size and loss is a 30% peak-to-peak ripple current  $\Delta I_L$  to the IC rated current. The switching frequency, input voltage, output voltage, and selected inductor ripple current determine the inductor value as follows:

$$L = \frac{V_{OUT} \times (V_{IN} - V_{OUT})}{V_{IN} \times f_{SW} \times \Delta I_L}$$

$$I_{L\_PEAK} = I_{OUT\_MAX} + \frac{1}{2} \Delta I_L$$

Larger inductance values result in lower output ripple voltage and higher efficiency, but slightly degraded transient response. Lower inductance values allow for a smaller case size, but the increased ripple lowers the effective current-limit threshold and increases the AC losses in the inductor. To enhance efficiency, choose a low-loss inductor with the lowest possible DC resistance that fits in the allotted dimensions. The inductor value determines the ripple current and the load-transient performance.

The selected inductor must have a sufficient saturation current rating above the peak inductor current before saturation. The peak inductor current ( $I_{L\_PEAK}$ ) is estimated as follows:

$$\Delta I_L = \frac{V_{OUT} \times (V_{IN} - V_{OUT})}{V_{IN} \times f_{SW} \times L}$$

$$I_{L\_PEAK} = I_{OUT\_MAX} + \frac{1}{2} \Delta I_L$$

The current flowing through the inductor is the inductor ripple current plus the output current. During power-up, faults, or transient load conditions, the inductor current can increase above the peak inductor current level calculated above. In transient conditions, the inductor current can increase up to the switch current limit of the device. For this reason, the most conservative approach is to specify an inductor with a saturation current rating equal to or greater than the switch current limit rather than the peak inductor current.

The reverse inductor current should be considered. The design of the inductor valley current should be higher than  $I_{L\_SNK}$  to prevent triggering the low-side switch sinking current limit during no-load operation.

### 18.3 Input Capacitor Selection

Input capacitance,  $C_{IN}$ , is needed to filter the pulsating current at the drain of the high-side power MOSFET. The  $C_{IN}$  should be sized to do this without causing a large variation in input voltage. The peak-to-peak voltage ripple on the input capacitor can be estimated using the following equation:

$$\Delta V_{CIN} = D \times I_{OUT} \times \frac{1-D}{C_{IN} \times f_{SW}} + I_{OUT} \times ESR$$

where

$$D = \frac{V_{OUT}}{V_{IN} \times \eta}$$

Figure 5 shows the  $C_{IN}$  ripple current flowing through the input capacitors and the resulting voltage ripple across the capacitors.

The equivalent series resistance (ESR) is very low for ceramic capacitors. The ripple caused by ESR can be ignored, and the minimum input capacitance can be estimated using the following equation:

$$C_{IN\_MIN} = I_{OUT\_MAX} \times \frac{D(1-D)}{\Delta V_{CIN\_MAX} \times f_{SW}}$$

where  $\Delta V_{CIN\_MAX} = 200\text{mV}$  for typical applications.

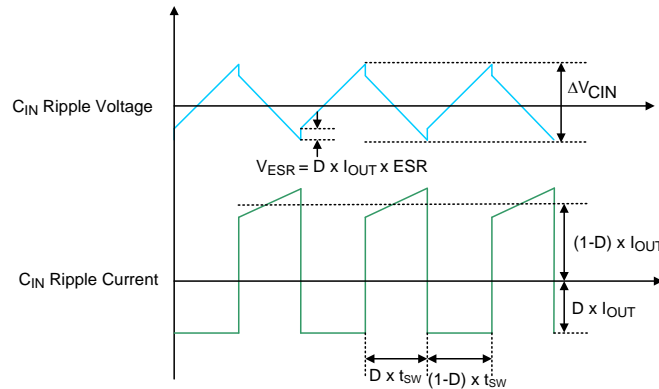


Figure 5.  $C_{IN}$  Ripple Voltage and Ripple Current

In addition, the input capacitor needs to have a very low ESR and must be rated to handle the worst-case RMS input current. The RMS ripple current ( $I_{RMS}$ ) of the converter can be determined by the input voltage ( $V_{IN}$ ), output voltage ( $V_{OUT}$ ), and rated output current ( $I_{OUT}$ ) as the following equation:

$$I_{RMS} \cong I_{OUT\_MAX} \times \frac{V_{OUT}}{V_{IN}} \times \sqrt{\frac{V_{IN}}{V_{OUT}} - 1}$$

From the above, the maximum RMS input ripple current occurs at maximum output load, which should be considered when evaluating the current capabilities of the input capacitors. The maximum ripple voltage usually occurs at 50% duty cycle, that is,  $V_{IN} = 2 \times V_{OUT}$ . It is common to use the worst-case  $I_{RMS} \cong 0.5 \times I_{OUT\_MAX}$  at  $V_{IN} = 2 \times V_{OUT}$  for design. Note that ripple current ratings from capacitor manufacturers are often based on only 2000 hours of life, which makes it advisable to further de-rate the capacitor, or choose a capacitor rated at a higher temperature than required.

Several capacitors may also be paralleled to meet size, height, and thermal requirements in the design. For low input voltage applications, sufficient bulk input capacitance is needed to minimize transient effects during output

load changes.

Ceramic capacitors are ideal for switching regulator applications because of their small size, robustness, and very low ESR. However, care must be taken when these capacitors are used at the input. A ceramic input capacitor combined with trace or cable inductance forms a high quality (under damped) tank circuit. If the RT5779A/B circuit is plugged into a live supply, the input voltage can ring to twice its nominal value, possibly exceeding the device's rating. This situation is easily avoided by placing the low ESR ceramic input capacitor in parallel with a bulk capacitor with higher ESR to damp the voltage ringing.

The input capacitor should be placed as close as possible to the VIN pins, with a low inductance connection to the GND of the IC. In addition to a larger bulk capacitor, one small ceramic capacitor of 0.1μF should be placed close to the part. The capacitors should be 0402 or 0603 in size. X7R capacitors are recommended for best performance across temperature and input voltage variations.

#### 18.4 Output Capacitor Selection

The selection of C<sub>OUT</sub> is determined by considering factors such as voltage ripple, transient loads, and ensuring that control loop is stable. Loop stability can be checked by viewing the load transient response. The peak-to-peak output ripple, ΔV<sub>OUT</sub>, is characterized by two components, which are ESR ripple ΔV<sub>P-P\_ESR</sub> and capacitive ripple ΔV<sub>P-P\_C</sub>, and can be expressed as follows:

$$\Delta V_{OUT} = \Delta V_{P-P\_ESR} + \Delta V_{P-P\_C}$$

$$\Delta V_{P-P\_ESR} = \Delta I_L \times R_{ESR}$$

$$\Delta V_{P-P\_C} = \frac{\Delta I_L}{8 \times C_{OUT} \times f_{SW}}$$

where the ΔI<sub>L</sub> is the peak-to-peak inductor ripple current and R<sub>ESR</sub> is the equivalent series resistance of C<sub>OUT</sub>. The highest output ripple is at maximum input voltage since ΔI<sub>L</sub> increases with input voltage. Multiple capacitors placed in parallel may be needed to meet the ESR and RMS current handling requirements.

Regarding the transient loads, the V<sub>SAG</sub> and V<sub>SOAR</sub> requirements should be taken into consideration for choosing the output capacitance value. The amount of output sag is a function of the maximum duty factor, which can be calculated from the on-time and minimum off-time.

$$t_{ON} = \frac{V_{OUT}}{V_{IN} \times f_{SW}}$$

$$D_{MAX} = \frac{t_{ON}}{t_{ON} + t_{OFF\_MIN}}$$

The worst-case output sag voltage can be determined by:

$$\Delta V_{OUT\_SAG} = \frac{L \times (I_{L\_PEAK})^2}{2 \times C_{OUT} \times (V_{IN} \times D_{MAX} - V_{OUT})}$$

The amount of overshoot due to stored inductor energy when the load is removed can be calculated as:

$$\Delta V_{OUT\_SOAR} = \frac{L \times (I_{L\_PEAK})^2}{2 \times C_{OUT} \times V_{OUT}}$$

Ceramic capacitors have very low equivalent series resistance (ESR) and provide the best ripple performance. Be careful to consider the voltage coefficient of ceramic capacitors when choosing the value and case size. Most ceramic capacitors lose 50% or more of their rated value when used near their rated voltage.

### 18.5 EN Pin for Start-Up and Shutdown Operation

For automatic start-up, the EN pin, with a high-voltage rating, can be connected to the input supply  $V_{IN}$ , either directly or through a  $100k\Omega$  resistor. The large built-in hysteresis band makes the EN pin useful for simple delay and timing circuits. The EN pin can be externally connected to  $V_{IN}$  by adding a resistor  $R_{EN}$  and a capacitor  $C_{EN}$ , as shown in [Figure 6](#) to have an additional delay. The time delay can be calculated with the EN's internal threshold, at which switching operation begins. An external MOSFET can be added for the EN pin to be logic-controlled, as shown in [Figure 7](#). In this case, a  $100k\Omega$  pull-up resistor,  $R_{EN}$ , is connected between  $V_{IN}$  and the EN pin. The MOSFET Q1 will be under logic control to pull down the EN pin. To prevent the device being enabled when  $V_{IN}$  is smaller than the  $V_{OUT}$  target level or some other desired voltage level, a resistive divider ( $R_{EN1}$  and  $R_{EN2}$ ) can be used to externally set the input undervoltage-lockout threshold, as shown in [Figure 8](#).

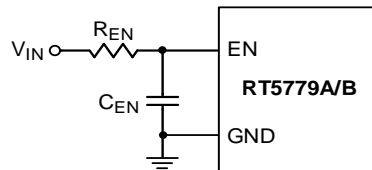


Figure 6. Enable Timing Control

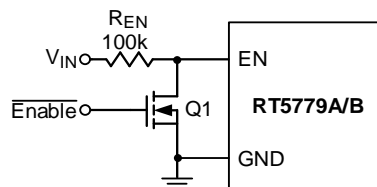


Figure 7. Logic Control for the EN Pin

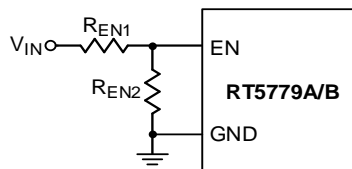


Figure 8. Resistor Divider for Undervoltage-Lockout Threshold Setting

### 18.6 Output Voltage Setting

The output voltage can be programmed by a resistive divider from the output to ground with the midpoint connected to the FB pin. The resistive divider allows the FB pin to sense a fraction of the output voltage, as shown in [Figure 9](#). The output voltage is set according to the following equation:

$$V_{OUT} = V_{TH\_FB} \times \left(1 + \frac{R_1}{R_2}\right)$$

where  $V_{TH\_FB}$  is around 0.6V (typical).

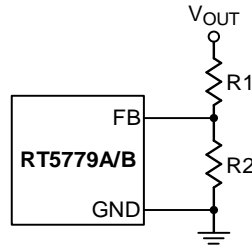


Figure 9. Output Voltage Setting

The placement of the resistive divider should be within 5mm of the FB pin. The resistance of R2 is suggested between 10kΩ and 100kΩ to minimize power consumption and noise pick-up at the FB pin. Once R2 is chosen, the resistance of R1 can then be obtained as follows:

$$R1 = \frac{R2 \times (V_{OUT} - V_{TH\_FB})}{V_{TH\_FB}}$$

For better output voltage accuracy, the divider resistors (R1 and R2) with  $\pm 1\%$  tolerance or better should be used.

### 18.7 Thermal Considerations

The junction temperature should never exceed the absolute maximum junction temperature  $T_{J(MAX)}$ , listed under Absolute Maximum Ratings, to avoid permanent damage to the device. The maximum allowable power dissipation depends on the thermal resistance of the IC package, the PCB layout, the rate of surrounding airflow, and the difference between the junction and ambient temperatures. The maximum power dissipation can be calculated using the following formula:

$$P_{D(MAX)} = (T_{J(MAX)} - T_A) / \theta_{JA}$$

where  $T_{J(MAX)}$  is the maximum junction temperature,  $T_A$  is the ambient temperature, and  $\theta_{JA(EVB)}$  is the junction-to-ambient thermal resistance.

For continuous operation, the maximum operating junction temperature indicated under Recommended Operating Conditions is 125°C. The junction-to-ambient thermal resistance,  $\theta_{JA(EVB)}$ , is highly package dependent. For a TSOT-23-8 (FC) package, the thermal resistance,  $\theta_{JA(EVB)}$ , is 73.9°C/W on a four-layer Richtek Evaluation Board. The maximum power dissipation at  $T_A = 25^\circ\text{C}$  can be calculated as follows:

$$P_{D(MAX)} = (125^\circ\text{C} - 25^\circ\text{C}) / (73.9^\circ\text{C/W}) = 1.35\text{W for a TSOT-23-8 (FC) package.}$$

The maximum power dissipation depends on the operating ambient temperature for the fixed  $T_{J(MAX)}$  and the thermal resistance,  $\theta_{JA(EVB)}$ . The derating curves in [Figure 10](#) allow the designer to see the effect of rising ambient temperature on the maximum power dissipation.

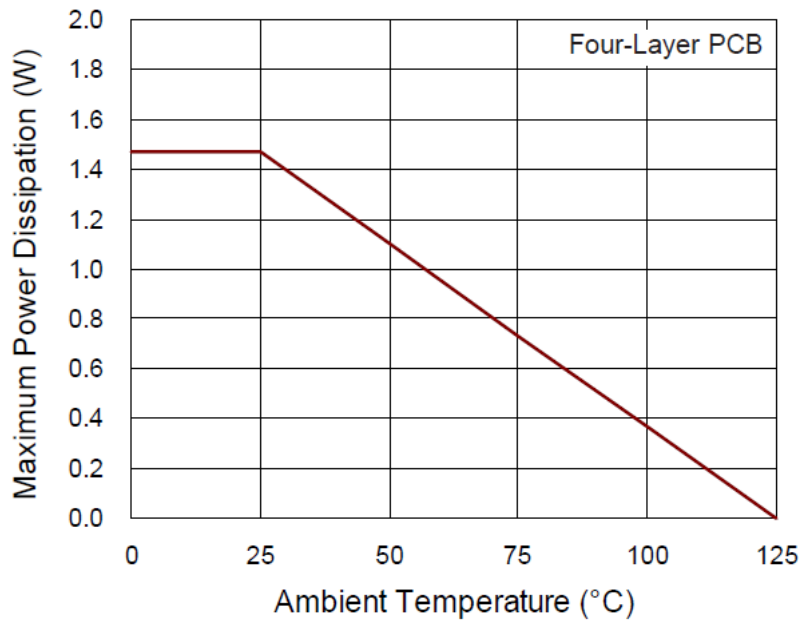


Figure 10. Derating Curve of Maximum Power Dissipation

### 18.8 Layout Considerations

Layout is very important in high-frequency switching converter design. The PCB can radiate excessive noise and contribute to converter instability with improper layout. Consider the following suggestions before starting a layout using the IC.

- Make traces of the high current paths as short and wide as possible.
- Put the input capacitor as close as possible to the device pins (VIN and GND).
- The SW node encounters high-frequency voltage swings, so it should be kept in a small area. Keep sensitive components away from the SW node to prevent stray as possible.
- The GND pin should be connected to a strong ground plane for heat sinking and noise protection.
- Avoid using vias in the power path connections that have switched currents (from CIN to GND and CIN to VIN) and the switching node (SW).

An example of PCB layout guide for a TSOT-23-8 (FC) is shown in [Figure 11](#).

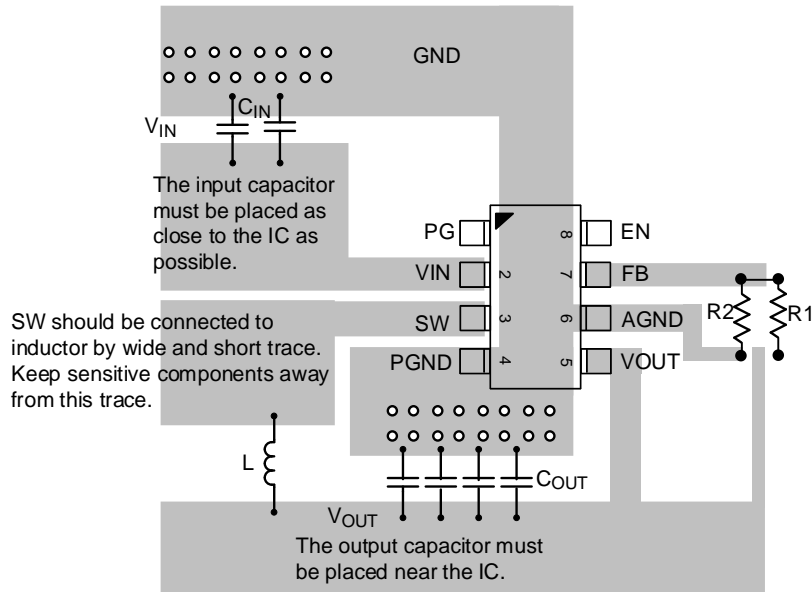
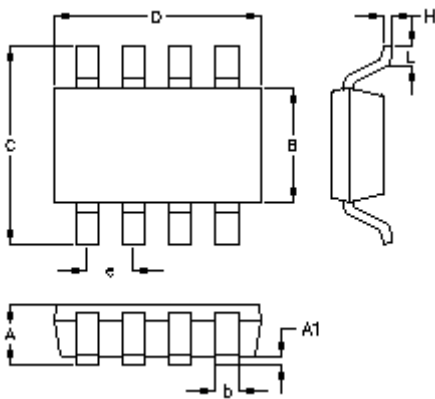


Figure 11. TSOT-23-8 (FC) PCB Layout Guide

**Note 7.** The information provided in this section is for reference only. The customer is solely responsible for the designing, validating, and testing your product incorporating Richtek's product and ensure such product meets applicable standards and any safety, security, or other requirements.

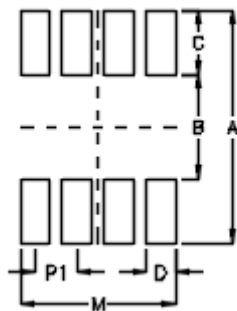
19 Outline Dimension



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	1.000	0.028	0.039
A1	0.000	0.100	0.000	0.004
B	1.397	1.803	0.055	0.071
b	0.220	0.380	0.009	0.015
C	2.591	3.000	0.102	0.118
D	2.692	3.099	0.106	0.122
e	0.585	0.715	0.023	0.028
H	0.080	0.254	0.003	0.010
L	0.300	0.610	0.012	0.024

TSOT-23-8 (FC) Surface Mount Package

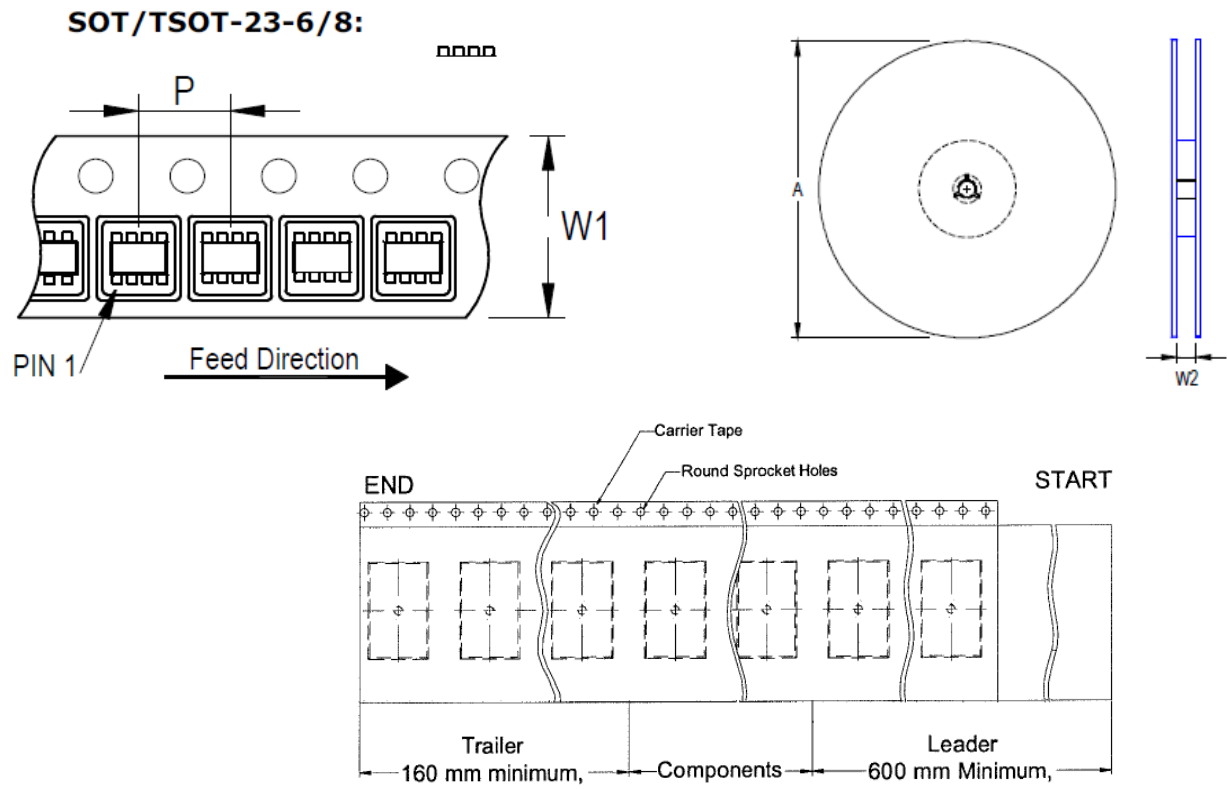
20 Footprint Information



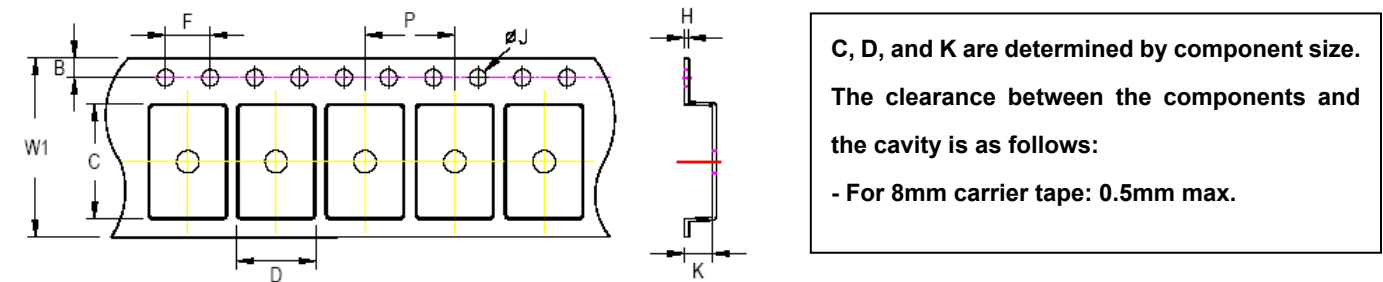
Package	Number of Pin	Footprint Dimension (mm)						Tolerance
		P1	A	B	C	D	M	
TSOT-28/TSOT-28(FC)/SOT-28	8	0.65	3.60	1.60	1.00	0.45	2.40	±0.10

21 Packing Information

21.1 Tape and Reel Data









Package Type	Tape Size (W1) (mm)	Pocket Pitch (P) (mm)	Reel Size (A)		Units per Reel	Trailer (mm)	Leader (mm)	Reel Width (W2) Min/Max (mm)
			(mm)	(in)				
TSOT-23-8	8	4	180	7	3,000	160	600	8.4/9.9



Tape Size	W1	P		B		F		ØJ		K		H
	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Max.
8mm	8.3mm	3.9mm	4.1mm	1.65mm	1.85mm	3.9mm	4.1mm	1.5mm	1.6mm	1.0mm	1.2mm	0.6mm

21.2 Tape and Reel Packing

Step	Photo/Description	Step	Photo/Description
1	 Reel 7"	4	 3 reels per inner box <b>Box A</b>
2	 HIC & Desiccant (1 Unit) inside	5	 12 inner boxes per outer box
3	 Caution label is on backside of Al bag	6	 Outer box <b>Carton A</b>

Container Package	Reel		Box			Carton		
	Size	Units	Item	Reels	Units	Item	Boxes	Unit
TSOT-23-8	7"	3,000	Box A	3	9,000	Carton A	12	108,000
			Box E	1	3,000	For Combined or Partial Reel.		

**21.3 Packing Material Anti-ESD Property**

Surface Resistance	Aluminum Bag	Reel	Cover tape	Carrier tape	Tube	Protection Band
$\Omega/\text{cm}^2$	$10^4 \text{ to } 10^{11}$	$10^4 \text{ to } 10^{11}$	$10^4 \text{ to } 10^{11}$	$10^4 \text{ to } 10^{11}$	$10^4 \text{ to } 10^{11}$	$10^4 \text{ to } 10^{11}$

22 Datasheet Revision History

Version	Date	Description	Item
02	2024/12/5	Modify	<i>Changed the names of pin 1 to PG</i> <i>General Description on page 1</i> <i>Features on page 1</i> <i>Ordering Information on page 2</i> <i>Electrical Characteristics on page 7, 8</i> <i>Operation on page 12 to 16</i> <i>Application Information on page 17 to 22</i> <i>Packing Information on page 26 to 28</i> - Added packing information